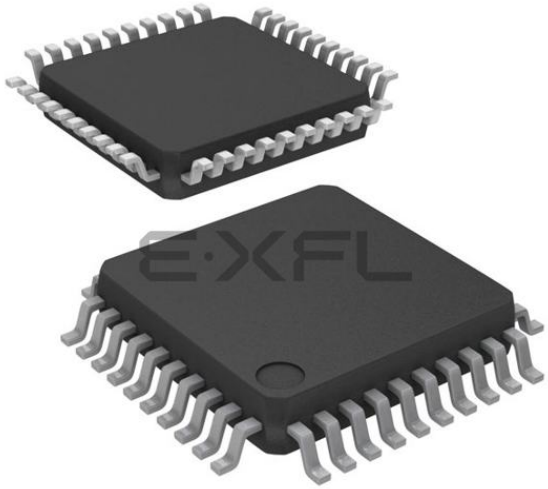
Renesas Electronics America Inc - R5F212E2NFP#W4 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	LINbus, SIO, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212e2nfp-w4

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1.1.2 Specifications

Tables 1.1 and 1.2 outlines the Specifications for R8C/2E Group and Tables 1.3 and 1.4 outlines the Specifications for R8C/2F Group.

Table 1.1 Specifications for R8C/2E Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.5 Product List for R8C/2E Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 2
I/O Ports	Programmable I/O ports	• Input-only: 3 pins • CMOS I/O ports: 25, selectable pull-up resistor • High current drive ports: 8
Clock	Clock generation circuits	2 circuits: XIN clock oscillation circuit (with on-chip feedback resistor), On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function) • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
Interrupts		• External: 4 sources, Internal: 13 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RE	8 bits × 1 Output compare mode
Serial Interface	UART0	Clock synchronous serial I/O/UART × 1
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function
D/A Converter		8-bit resolution × 2 circuits
Comparator		2 circuits

Table 1.2 Specifications for R8C/2E Group (2)

Item	Specification
Flash Memory	• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 100 times • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function
Operating Frequency/Supply Voltage	f(XIN) = 20 MHz (VCC = 3.0 to 5.5 V), f(XIN) = 10 MHz (VCC = 2.7 to 5.5 V)
Current consumption	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 23 μA (VCC = 3.0 V, wait mode (peripheral clock off)) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature	-20 to 85°C (N version) -40 to 85°C (D version)(1)
Package	32-pin LQFP Package code: PLQP0032GB-A (previous code: 32P6U-A)

NOTE:
1. Specify the D version if D version functions are to be used.

Table 1.6 Product List for R8C/2F Group **Current of Dec. 2007**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F212F2NFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version
R5F212F4NFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	
R5F212F2DFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version
R5F212F4DFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	
R5F212F2NXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version
R5F212F4NXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	Factory programming product(1)
R5F212F2DXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version
R5F212F4DXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	Factory programming product(1)

NOTE:
1. The user ROM is programmed before shipment.

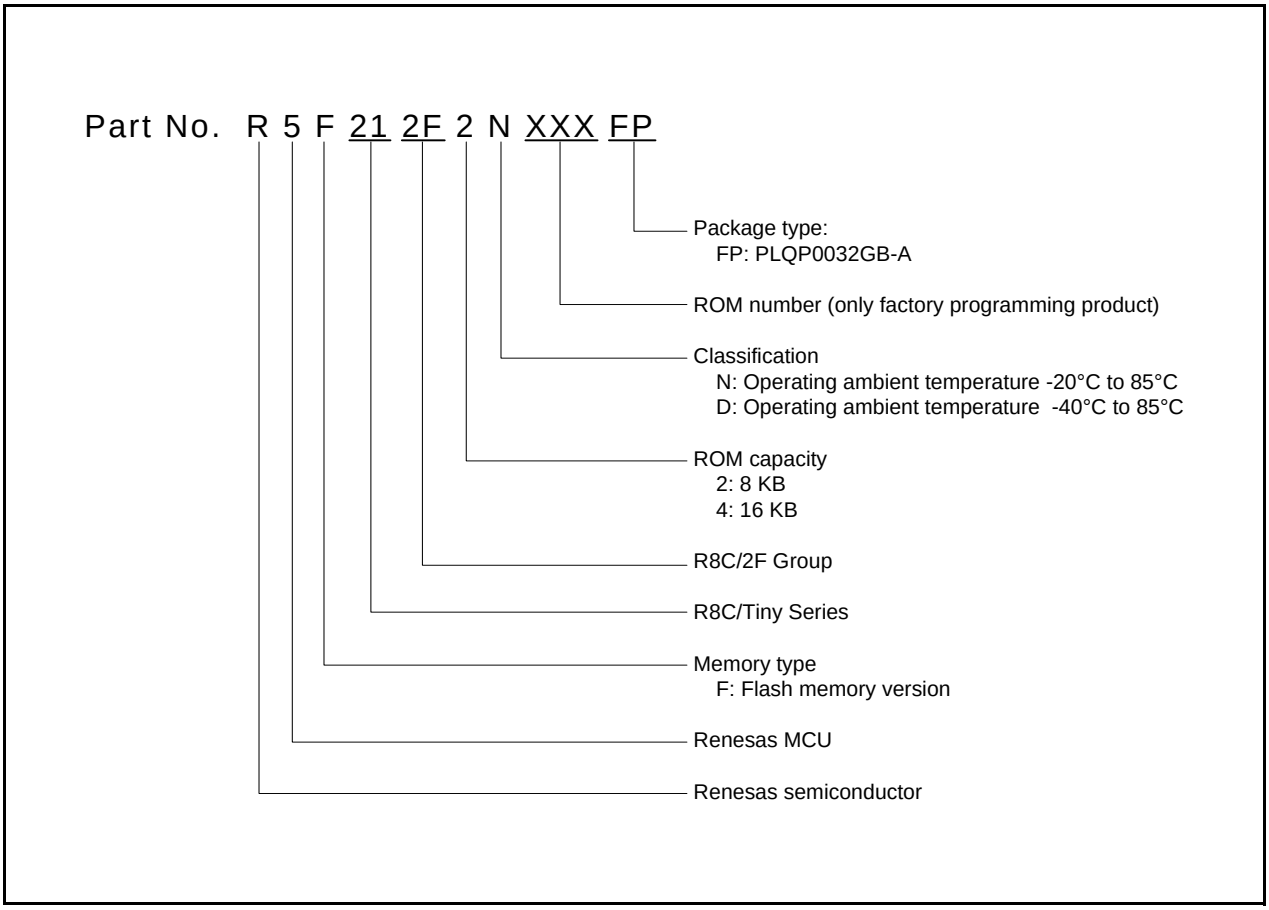
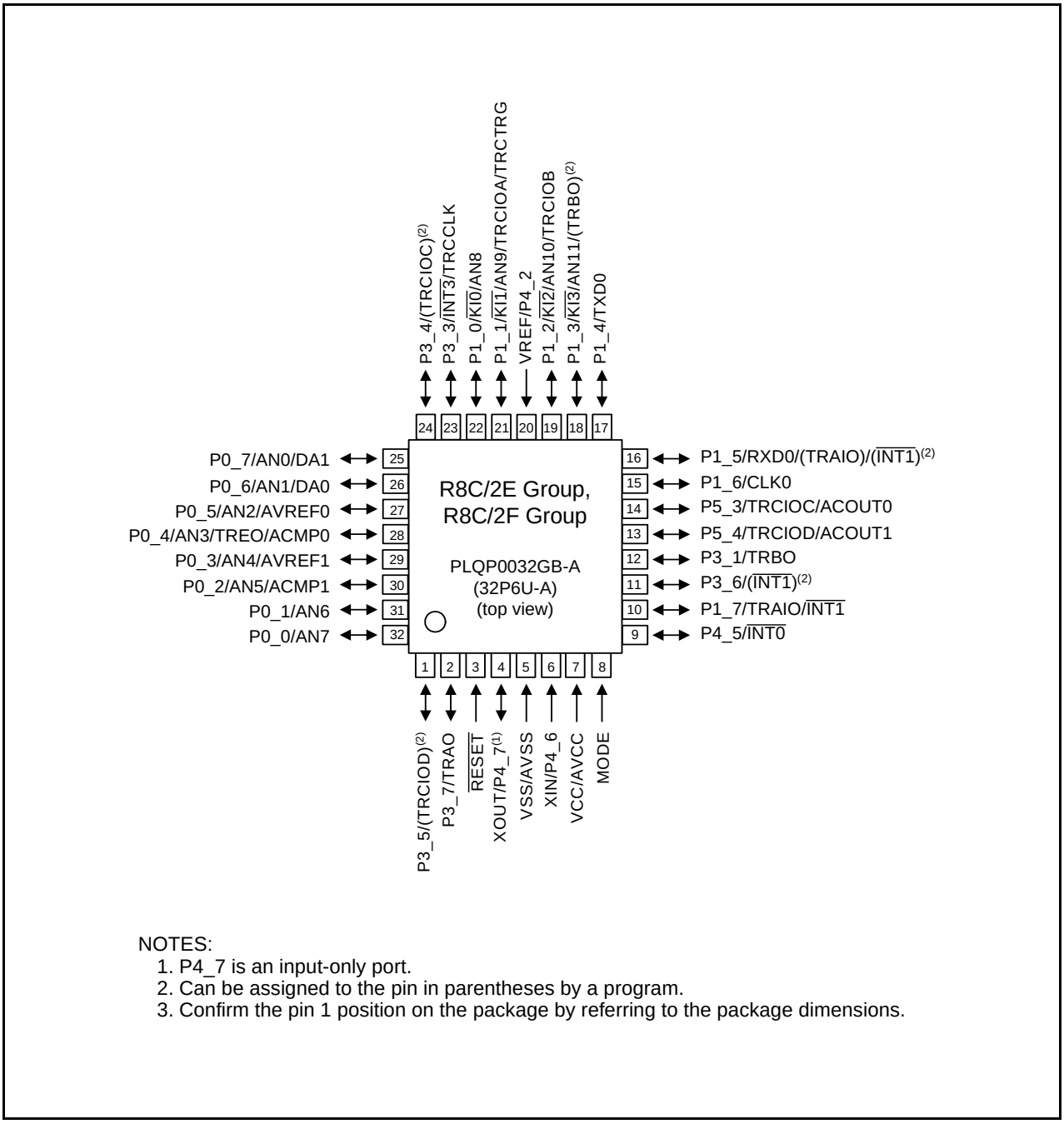


Figure 1.2 Part Number, Memory Size, and Package of R8C/2F Group

1.4 Pin Assignment

Figure 1.4 shows Pin Assignments (Top View). Table 1.7 outlines the Pin Name Information by Pin Number.

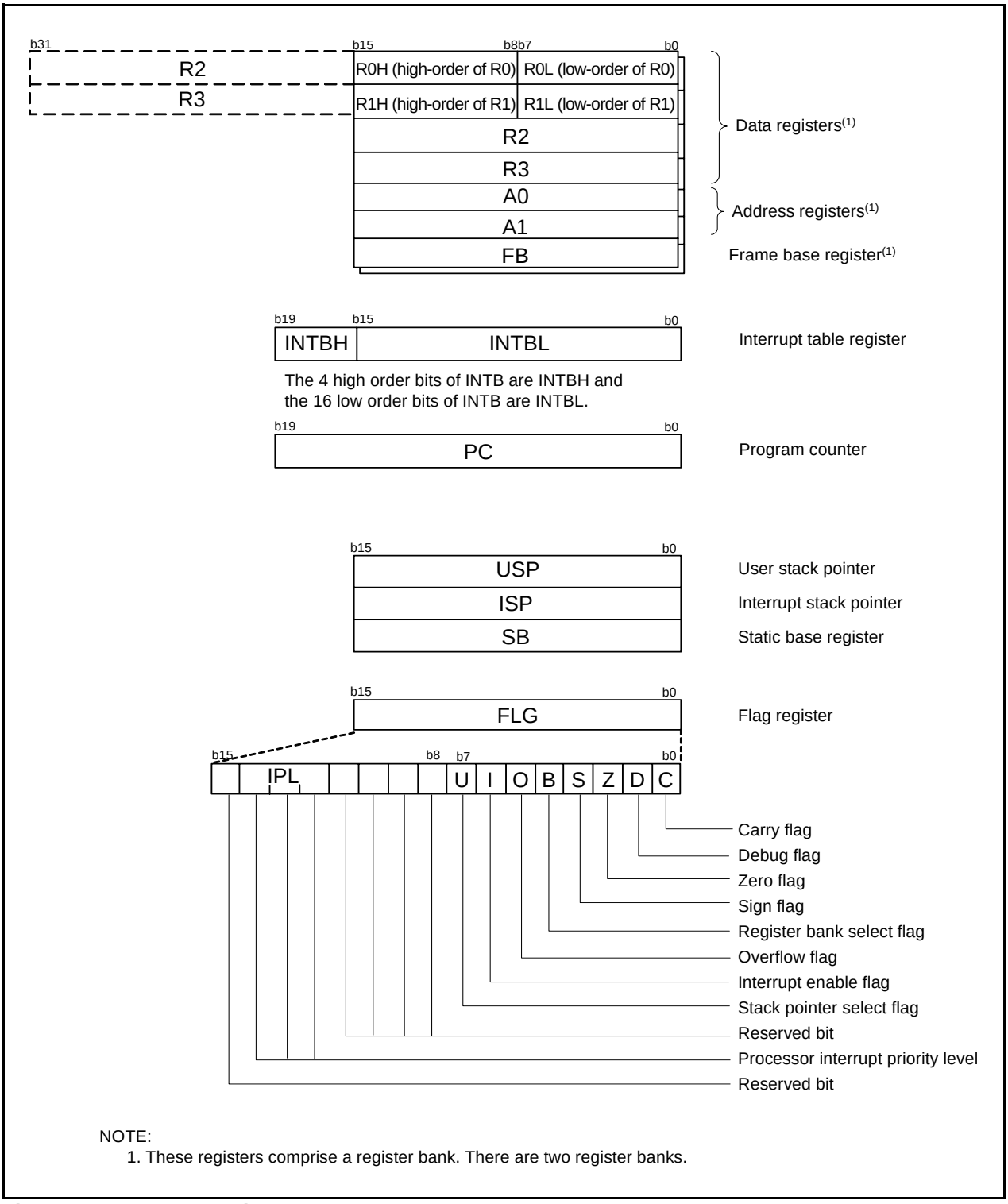


NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 to be used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupt are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

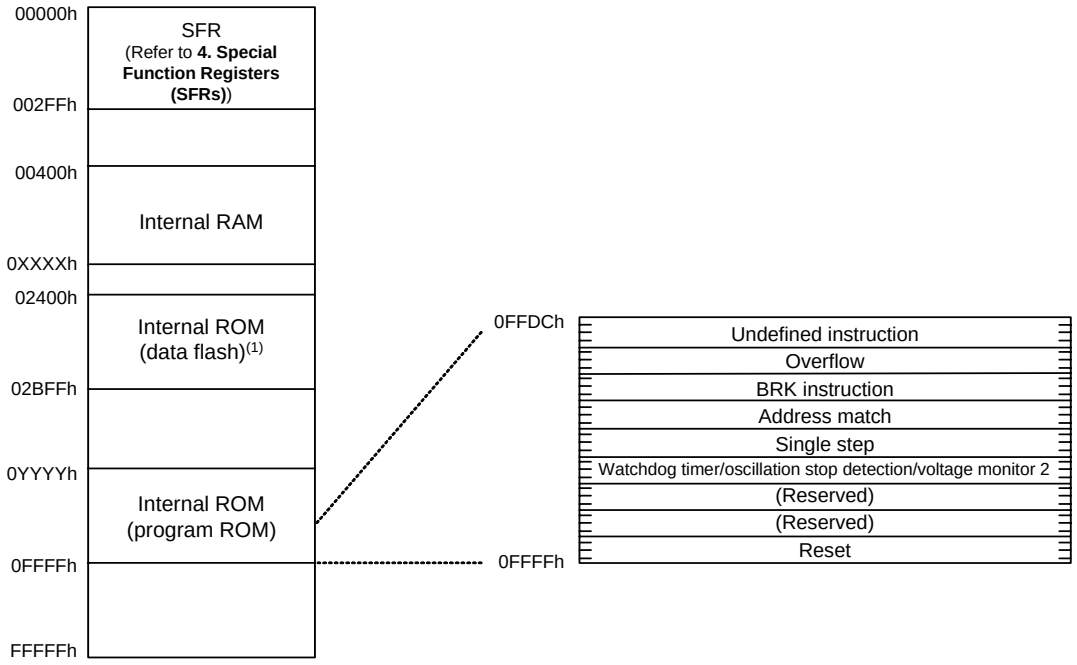
IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3.2 R8C/2F Group

Figure 3.2 is a Memory Map of R8C/2F Group. The R8C/2F group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F212F2NFP, R5F212F2DFP, R5F212F2NXXXFP, R5F212F2DXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F212F4NFP, R5F212F4DFP, R5F212F4NXXXFP, R5F212F4DXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh

Figure 3.2 Memory Map of R8C/2F Group

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h			
0089h			
008Ah			
008Bh			
008Ch			
008Dh			
008Eh			
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h			
00A9h			
00AAh			
00ABh			
00ACh			
00ADh			
00AEh			
00AFh			
00B0h			
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh			
00BCh			
00BDh			
00BEh			
00BFh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.4 SFR Information (4)(1)

Address	Register	Symbol	After reset
00C0h	A/D Register	AD	XXh
00C1h			XXh
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Control Register 2	ADCON2	00h
00D5h			
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h	D/A Register 0	DA0	00h
00D9h			
00DAh	D/A Register 1	DA1	00h
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	00h
00E1h	Port P1 Register	P1	00h
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h			
00E5h	Port P3 Register	P3	00h
00E6h			
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	00h
00E9h	Port P5 Register	P5	00h
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh			
00EDh			
00EEh			
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h	Pin Select Register 2	PINSR2	00h
00F7h	Pin Select Register 3	PINSR3	00h
00F8h	Port Mode Register	PMR	00h
00F9h	External Input Enable Register	INTEN	00h
00FAh	INT Input Filter Select Register	INTF	00h
00FBh	Key Input Enable Register	KIEN	00h
00FCh	Pull-Up Control Register 0	PUR0	00h
00FDh	Pull-Up Control Register 1	PUR1	00h
00FEh	Port P1 Drive Capacity Control Register	P1DRR	00h
00FFh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.5 SFR Information (5)(1)

Address	Register	Symbol	After reset
0100h	Timer RA Control Register	TRACR	00h
0101h	Timer RA I/O Control Register	TRAIOC	00h
0102h	Timer RA Mode Register	TRAMR	00h
0103h	Timer RA Prescaler Register	TRAPRE	FFh
0104h	Timer RA Register	TRA	FFh
0105h			
0106h	LIN Control Register	LINCR	00h
0107h	LIN Status Register	LINST	00h
0108h	Timer RB Control Register	TRBCR	00h
0109h	Timer RB One-Shot Control Register	TRBOCR	00h
010Ah	Timer RB I/O Control Register	TRBIOC	00h
010Bh	Timer RB Mode Register	TRBMR	00h
010Ch	Timer RB Prescaler Register	TRBPRE	FFh
010Dh	Timer RB Secondary Register	TRBSC	FFh
010Eh	Timer RB Primary Register	TRBPR	FFh
010Fh			
0110h			
0111h			
0112h			
0113h			
0114h			
0115h			
0116h			
0117h			
0118h	Timer RE Counter Data Register	TRESEC	00h
0119h	Timer RE Compare Data Register	TREMIN	00h
011Ah			
011Bh			
011Ch	Timer RE Control Register 1	TRECR1	00h
011Dh	Timer RE Control Register 2	TRECR2	00h
011Eh	Timer RE Clock Source Select Register	TRECSR	00001000b
011Fh			
0120h	Timer RC Mode Register	TRCMR	01001000b
0121h	Timer RC Control Register 1	TRCCR1	00h
0122h	Timer RC Interrupt Enable Register	TRCIER	01110000b
0123h	Timer RC Status Register	TRCSR	01110000b
0124h	Timer RC I/O Control Register 0	TRCIOR0	10001000b
0125h	Timer RC I/O Control Register 1	TRCIOR1	10001000b
0126h	Timer RC Counter	TRC	00h
0127h			00h
0128h	Timer RC General Register A	TRCGRA	FFh
0129h			FFh
012Ah	Timer RC General Register B	TRCGRB	FFh
012Bh			FFh
012Ch	Timer RC General Register C	TRCGRC	FFh
012Dh			FFh
012Eh	Timer RC General Register D	TRCGRD	FFh
012Fh			FFh
0130h	Timer RC Control Register 2	TRCCR2	00011111b
0131h	Timer RC Digital Filter Function Select Register	TRCDF	00h
0132h	Timer RC Output Master Enable Register	TRCOER	01111111b
0133h			
0134h			
0135h			
0136h			
0137h			
0138h			
0139h			
013Ah			
013Bh			
013Ch			
013Dh			
013Eh			
013Fh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 5.7 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		–20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. –40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

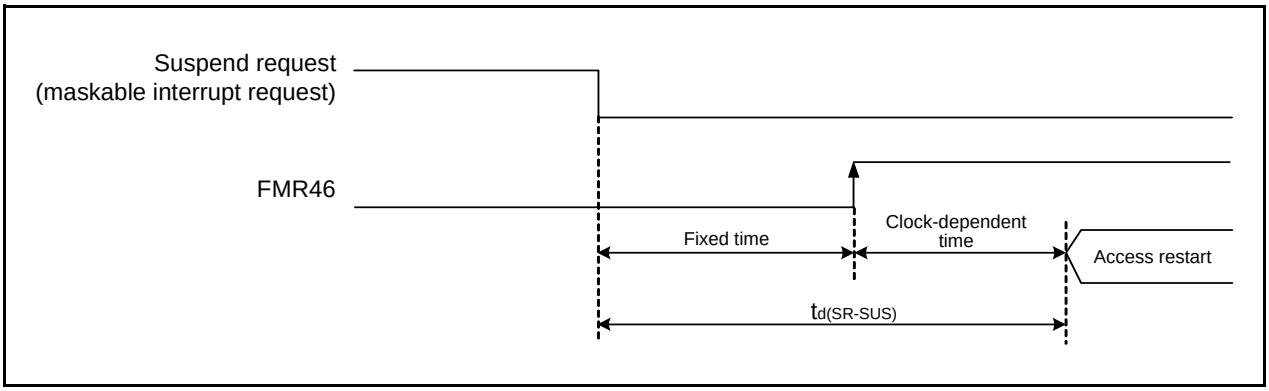


Figure 5.2 Time delay until Suspend

Table 5.8 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(4)		2.7	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.9 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.11 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V 0°C ≤ T_{opr} ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 2.7 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C(2)	38	40	42	MHz
		V_{CC} = 2.7 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C(2)	37.6	40	42.4	MHz
		V_{CC} = 5.0 V ±10% –20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	40.8	MHz
		V_{CC} = 5.0 V ±10% –40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	40.8	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register	V_{CC} = 5.0 V, T_{opr} = 25°C	–	36.864	–	MHz
		V_{CC} = 2.7 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	–3%	–	3%	%
–	Value in FRA1 register after reset		08h	–	F7h	–
–	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to –1	–	+0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

NOTES:
1. V_{CC} = 2.7 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.

Table 5.12 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.7 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.13 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.15 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0 VCA20 = 1	–	25	75	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0 VCA20 = 1	–	23	60	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.8	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	1.2	–	µA

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.16 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

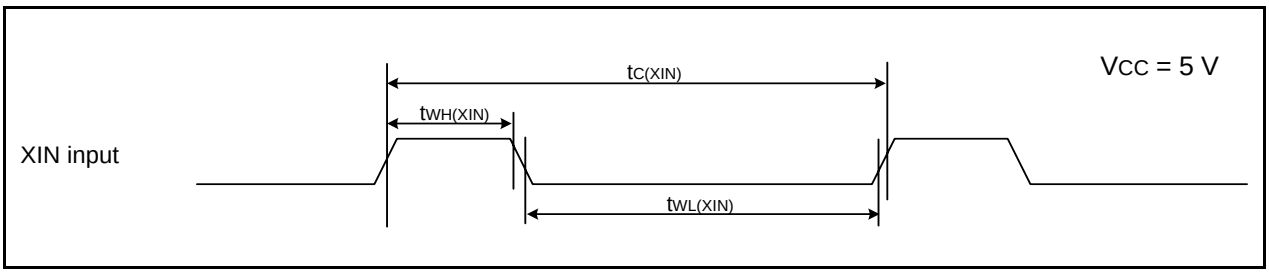


Figure 5.4 XIN Input Timing Diagram when V_{CC} = 5 V

Table 5.17 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

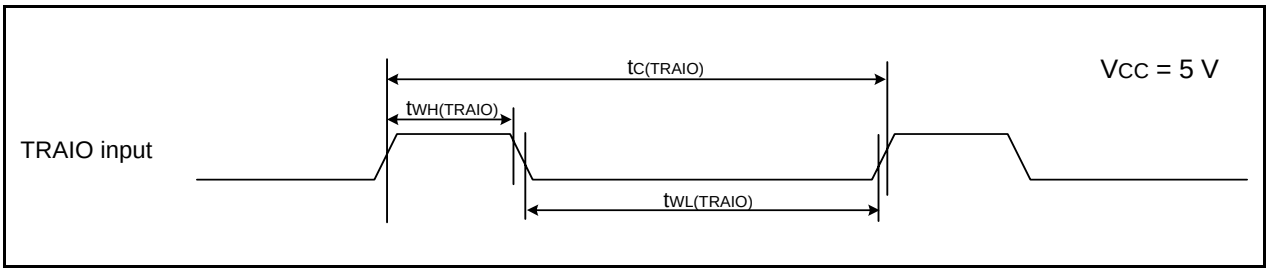


Figure 5.5 TRAIO Input Timing Diagram when V_{CC} = 5 V

Table 5.18 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLK0 input cycle time	200	–	ns
$t_{W(CKH)}$	CLK0 input “H” width	100	–	ns
$t_{W(CKL)}$	CLK0 input “L” width	100	–	ns
$t_{d(C-Q)}$	TXD0 output delay time	–	50	ns
$t_{h(C-Q)}$	TXD0 hold time	0	–	ns
$t_{su(D-C)}$	RXD0 input setup time	50	–	ns
$t_{h(C-D)}$	RXD0 input hold time	90	–	ns

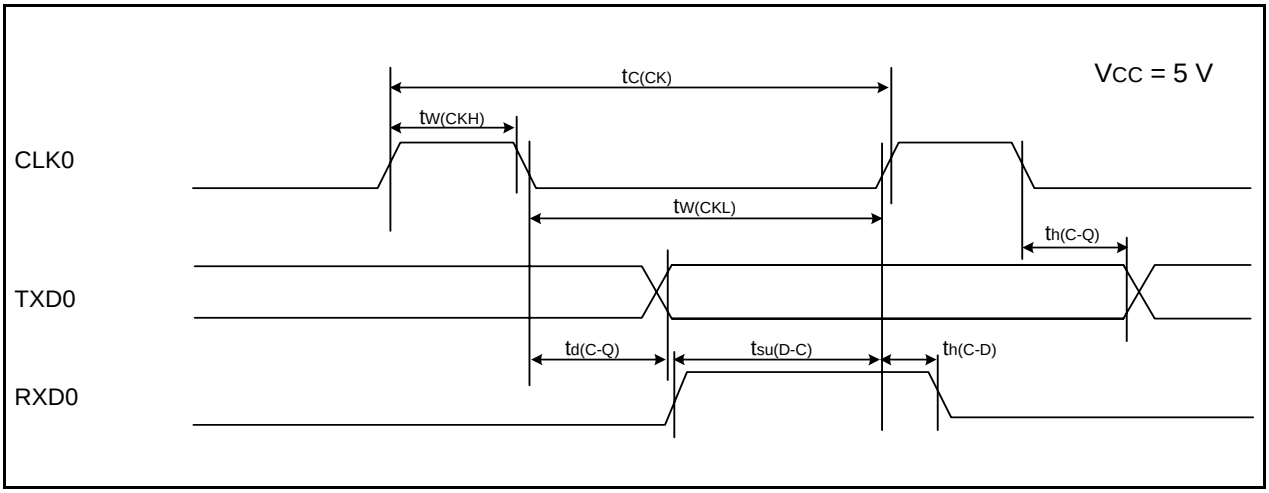


Figure 5.6 Serial Interface Timing Diagram when VCC = 5 V

Table 5.19 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

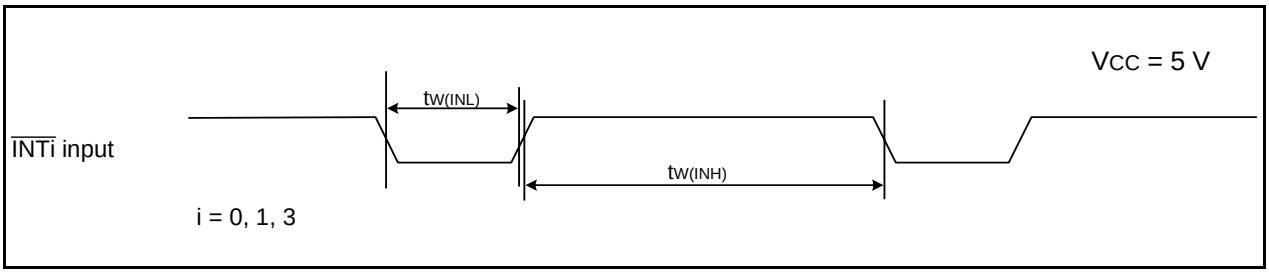


Figure 5.7 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 5 V

Table 5.20 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = –1 mA		V_{CC} – 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = –0.1 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –50 μA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, CLK0			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} =2.7 to 3.3 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), $f_{(XIN)}$ = 10 MHz, unless otherwise specified.

Table 5.24 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLK0 input cycle time	300	–	ns
$t_{W(CKH)}$	CLK0 input “H” width	150	–	ns
$t_{W(CKL)}$	CLK0 Input “L” width	150	–	ns
$t_{d(C-Q)}$	TXD0 output delay time	–	80	ns
$t_{h(C-Q)}$	TXD0 hold time	0	–	ns
$t_{su(D-C)}$	RXD0 input setup time	70	–	ns
$t_{h(C-D)}$	RXD0 input hold time	90	–	ns

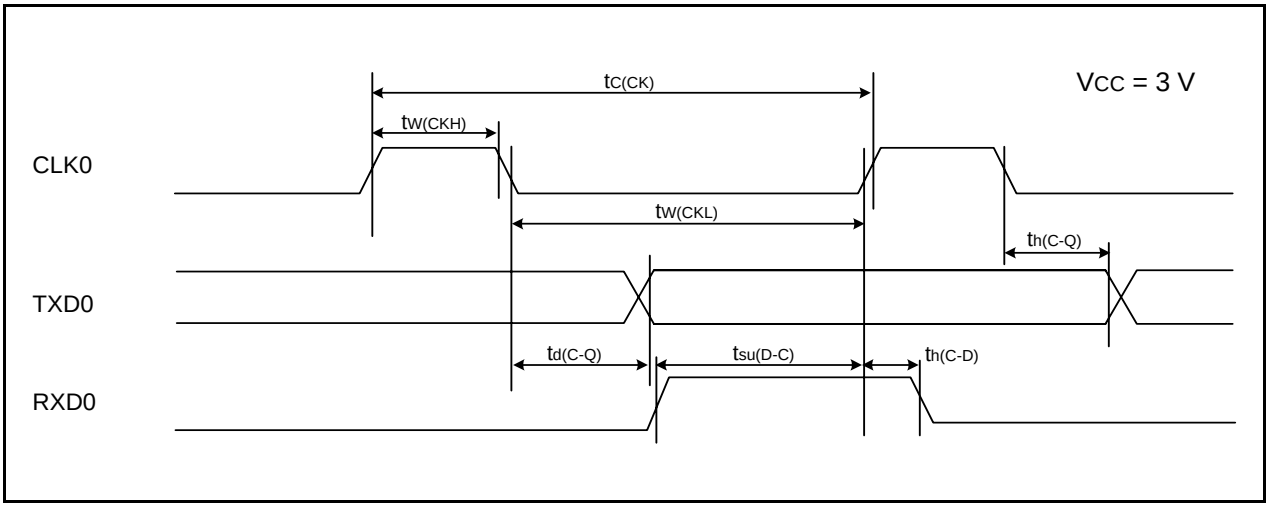


Figure 5.10 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.25 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

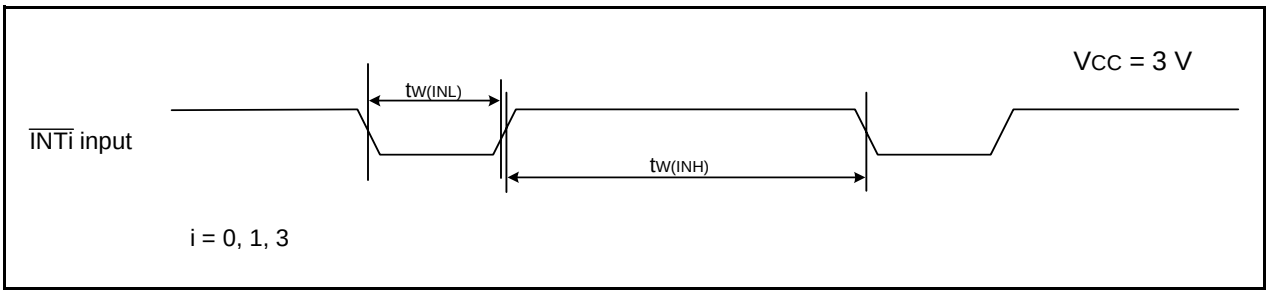


Figure 5.11 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 3 V